



Product Discontinuation Notices

December 1, 2009

Photomicro Sensors

No. 2009304E

Discontinuation Notice of Photomicrosensors. EE-SB5V series

Product Discontinuation

Recommended Replacement



EE-SB5V Series



Please contact the appropriate division EE-SY672 (except the EE-SB5M-E)

Discontinuation date : The end of May, 2010

Caution on recommended replacement

Our Amplified photomicrosensors, model EE-SB5V series will be discontinued at the end of May, 2010. We recommend Amplified photomicrosensors, type EE-SY672 for replacement of them (except the EE-SB5V-E). And we recommend to change your products design or to order it collectively including a necessary amount in the future by May, 2010.

Difference from discontinued product

Model	Body Color	Dimen sions	Wire connection	Mounting Dimensions	Charact eristics	Operation ratings	Operation methods
EE-SY672	**	*		*	*	*	**

** : Fully compatible

* : The change is a little/Almost compatible

-- : Not compatible

- : No corresponding specification

Product Discontinuation and recommended replacement

Product disc	ontinuation	Recommended replacement		
Model	Product code	Model	Product code	
EE-SB5V	EESB1010G	EE-SY672	EESY1124M	
EE-SB5V-F	EESB5052D	No recommended replacement		
EE-SB5V-P1	EESB5054M	EE-SY672	EESY1124M	
EE-SB5VC	EESB2010B	EE-SY672	EESY1124M	

Dimensions





Internal connection



Characteristics

Item		Product discontinuation		Recommended replacement	
		EE-SB5V	EE-SB5VC	EE-SY672	
Sonoing distance		5mm		1 to 5mm	
Sensing distance		(Reflection factor 90%)		(Reflection factor 90%)	
Differential		0.1mm		0.5mm	
Light sourc	e	GaAs infrared LED		GaAs infrared LED	
Supply volt	ane	5-10% to 15+10% VDC		5-10% to 24+10% VDC	
	-	Ripple (p-p): 10% MAX.		Ripple (p-p): 10% MAX.	
Current cor	nsumption	48mA MAX.		40mA MAX.	
		Load power supply voltage:		Load power supply voltage:	
		5 to 24VDC		5 to 24VDC	
Control out	put	80mA load current with a residual		100mA load current with a residual	
		voltage 0.8V MAX.		voltage 0.8V MAX.	
		40mA load current with a residual		40mA load current with a residual	
	Otana af autout	voltage 0.4V MAX.		voltage 0.4V MAX	
	Stage of output	OFF	ON	OFF (Terminal []] ia	ON (Terminal []] ia
Channe of	transistor when			(Terminal [L] is	(Terminal [L] is
Stage of output	object is not sensed			short-circuited)	opened)
transistor	Stage of output	ON	OFF	ON	OFF
แลกรารเบา	transistor when	ON	OFF	(Terminal [L] is	(Terminal [L] is
	object is sensed			short-circuited)	opened)
Response frequency		50Hz		50Hz	openedy
•	, ,	Operating : -25 to +55°C		Operating : -25 to +55°C	
Ambient te	mperature range	Storage : -30 to +80°C		Storage : -30 to +80°C	
		Operating: 45 to 85%RH		Operating : 5 to 85%RH	
Ambient hu	imidity range	Storage : 35 to 95%RH		Storage : 5 to 95%RH	
Vibration resistance		Destruction:		Destruction:	
		20 to 2000 Hz		20 to 2000 Hz	
		(Peak acceleration: 200m/s ²)		(Peak acceleration: 100m/s ²)	
VIDIATION IC	5313101100	1.5mm double amplitude for		1.5mm double amplitude for 2h	
		4cycle (4min periods) each in X, Y		(4min periods) each in X, Y and Z	
		and Z directions		directions	
		Destruction:		Destruction:	
Shock resistance		15000m/S^2 for 3 times each in X,		500m/S^2 for 3 times each in X, Y	
		Y and Z directions		and Z directions	

Characteristics

Item		Product discontinuation EE-SB5V-P1	Recommended replacement EE-SY672		
Sensing distance		5mm	1 to 5mm		
		(Reflection factor 90%)	(Reflection factor 90%)		
Differential of		0.1mm	0.5mm		
Light source	9	GaAs infrared LED	GaAs infrared LED		
Supply volta	age	24±10% VDC	5-10% to 24+10% VDC		
			Ripple (p-p): 10% MAX.		
Current con	sumption	-	40mA MAX.		
		Load power supply voltage:	Load power supply voltage:		
		5 to 24VDC	5 to 24VDC		
Control outp	but	10mA load current with a residual	100mA load current with a residual		
		voltage 0.3V MAX.	voltage 0.8V MAX. 40mA load current with a residual		
	Store of output	OFF	voltage 0.4V MAX	^. ON	
	Stage of output transistor when	OFF	-	(Terminal [L] is	
			(Terminal [L] is short-circuited)	opened)	
Stage of	object is not sensed		short-circuited)	opened)	
output	Stage of output	ON	ON	OFF	
transistor	transistor when		(Terminal [L] is	(Terminal [L] is	
	object is		short-circuited)	opened)	
	sensed			oponou)	
Response frequency		50Hz	50Hz		
		Operating : -25 to +55°C	Operating : -25 to +55°C		
Ambient ten	nperature range	Storage : -30 to +80°C	Storage : -30 to +80°C		
Amplianthu		Operating: 45 to 85%RH	Operating : 5 to 85%RH		
Ambient humidity range		Storage : 35 to 95%RH	Storage 5 to 95%RH		
Vibration resistance		Destruction:	Destruction:		
		20 to 2000 Hz	20 to 2000 Hz		
		(Peak acceleration: 200m/s ²)	(Peak acceleration: 100m/s ²)		
		1.5mm double amplitude for	1.5mm double amplitude for 2h		
		4cycle (4min periods) each in X,	(4min periods) each in X, Y and Z		
		Y and Z directions	directions		
Shock resistance		Destruction:	Destruction:		
		15000m/S ² for 3 times each in X,	500m/S^2 for 3 times each in X, Y		
		Y and Z directions	and Z directions		

Characteristics					
ltem		Product discontinuation EE-SB5V-E	Recommended replacement No type		
Sensing distance		19mm (Reflection factor 90%)	/		
Differential dista	ance	0.1mm	/		
Light source		GaAs infrared LED	/		
Supply voltage		5-10% to 15+10% VDC Ripple (p-p): 10% MAX.			
Current consun	nption	48mA MAX.			
Control output		Load power supply voltage: 5 to 24VDC 80mA load current with a residual voltage 0.8V MAX. 40mA load current with a residual voltage 0.4V MAX.			
Stage of output transistor	Stage of output transistor when object is not sensed Stage of output transistor when object is sensed	OFF ON			
Response frequ		50Hz			
Ambient tempe		Operating : -25 to +55°C Storage : -30 to +80°C			
Ambient humid	ty range	Operating: 45 to 85%RH Storage: 85 to 95%RH			
Vibration resistance		Destruction: 20 to 2000 Hz (Peak acceleration: 200m/s ²) 1.5mm double amplitude for 4cycle (4min periods) each in X, Y and Z directions			
Shock resistance		Destruction: 15000m/S ² for 3 times each in X, Y and Z directions			